

General Description

The WST3052 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST3052 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

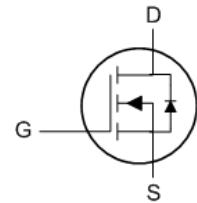
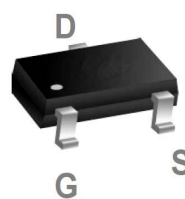
Product Summary

BVDSS	RDSON	ID
30V	60mΩ	2.5A

Applications

- Power Management in Notebook Computer Portable Equipment and Battery Powered Systems.

SOT-323 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	2.5	A
$I_D@T_c=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	2.0	A
I_{DM}	Pulsed Drain Current ²	13	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	0.7	W
$P_D@T_A=70^\circ C$	Total Power Dissipation ³	0.45	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	180	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ ($t \leq 10s$)	---	120	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	100	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.025	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =2.5A	---	50	60	mΩ
		V _{GS} =2.5V, I _D =2A	---	60	70	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.5	0.7	1.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.8	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	30	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =2A	---	7	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.5	5	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =10V, V _{GS} =4.5V, I _D =1A	---	4.0	8.4	nC
Q _{gs}	Gate-Source Charge		---	0.3	3.5	
Q _{gd}	Gate-Drain Charge		---	1.5	2.9	
T _{d(on)}	Turn-On Delay Time	V _{DD} =10V, V _{GS} =10V, R _G =6Ω, I _D =1A, R _L =10Ω.	---	3.5	5.2	ns
T _r	Rise Time		---	13.3	21	
T _{d(off)}	Turn-Off Delay Time		---	13.2	20	
T _f	Fall Time		---	2	5	
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	---	286	---	pF
C _{oss}	Output Capacitance		---	60	---	
C _{rss}	Reverse Transfer Capacitance		---	50	---	

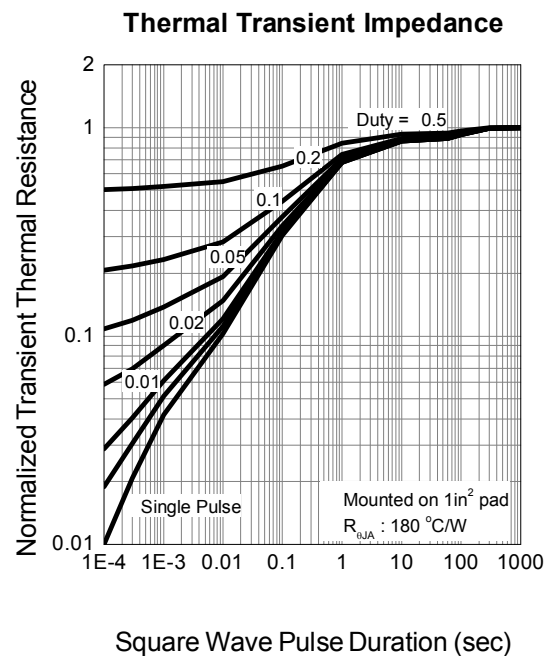
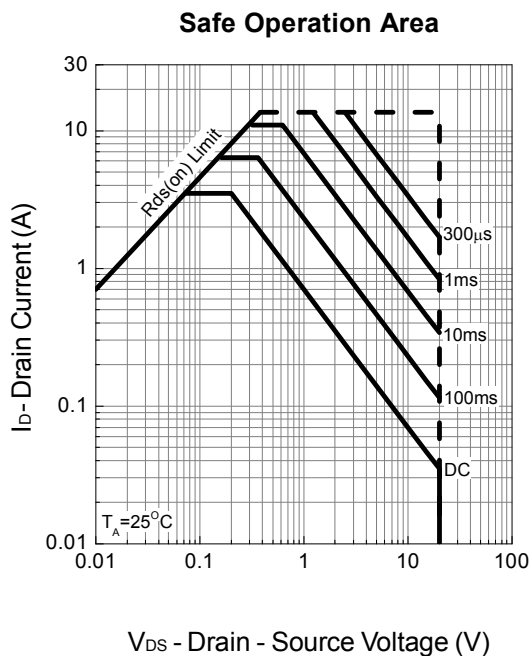
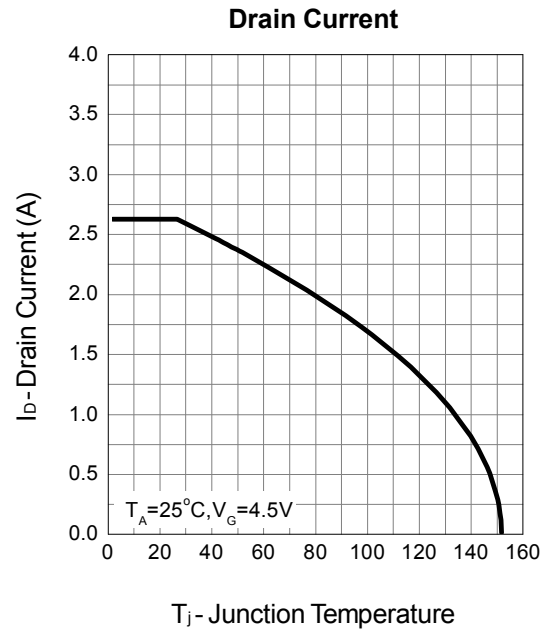
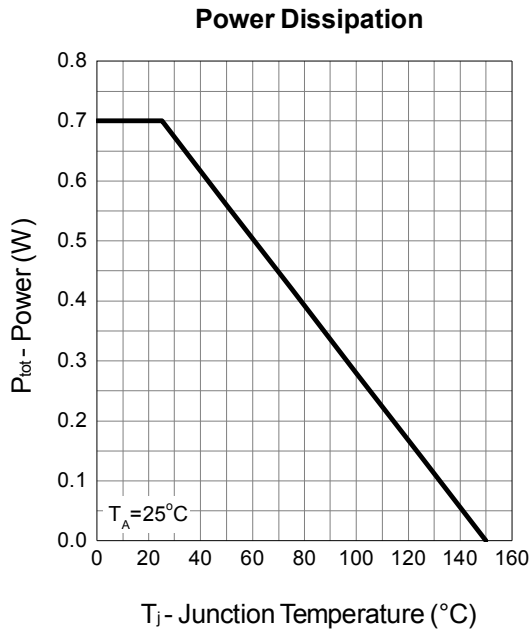
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	2.5	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	13	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.0	V
t _{rr}	Reverse Recovery Time	I _F =5A, di/dt=100A/μs, T _J =25°C	---	15	---	nS
Q _{rr}	Reverse Recovery Charge		---	3.7	---	nC

Note :

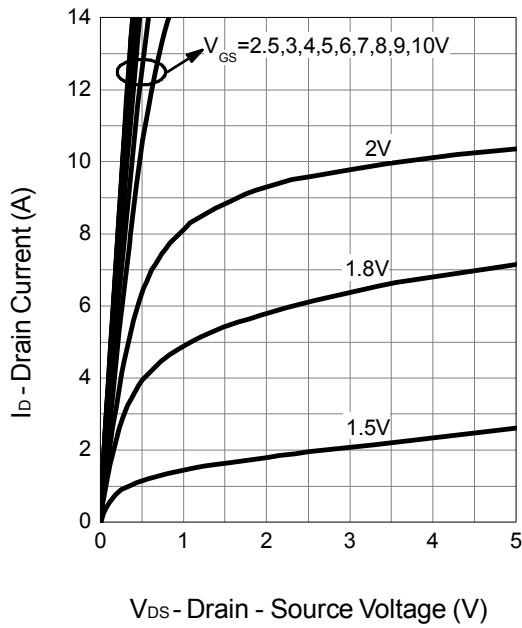
- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

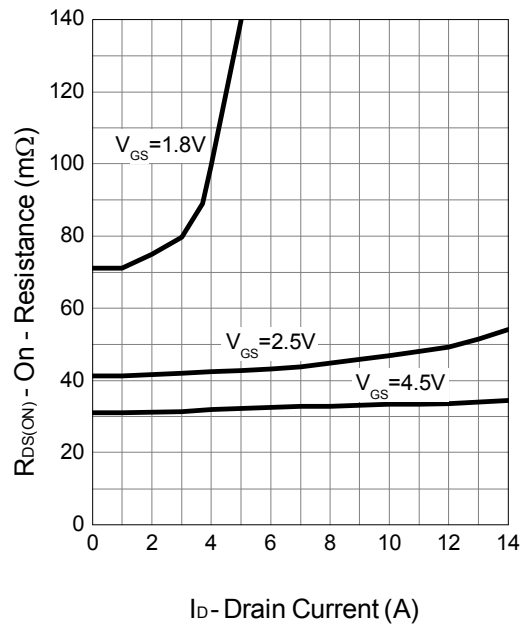


Typical Characteristics

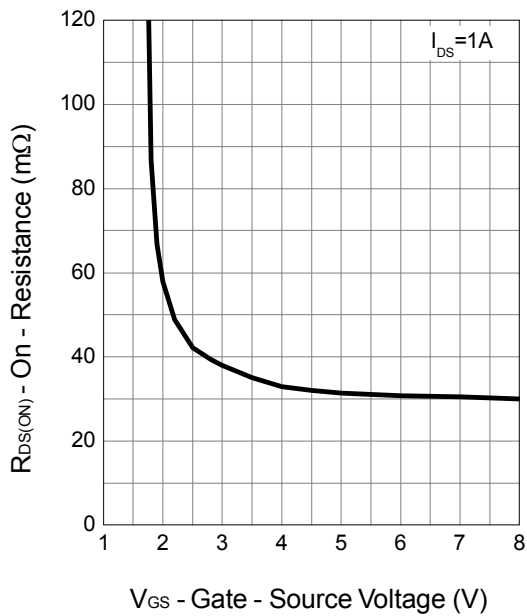
Output Characteristics



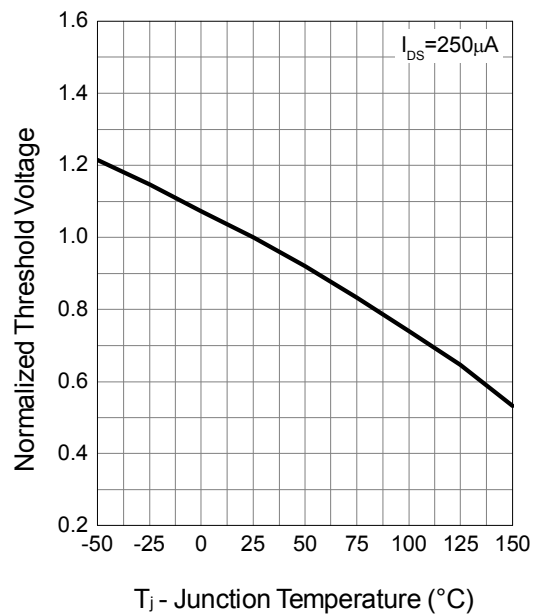
Drain-Source On Resistance



Gate-Source On Resistance

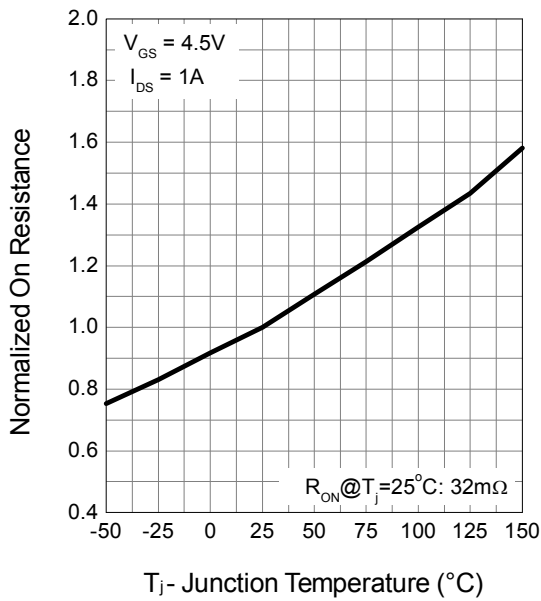


Gate Threshold Voltage

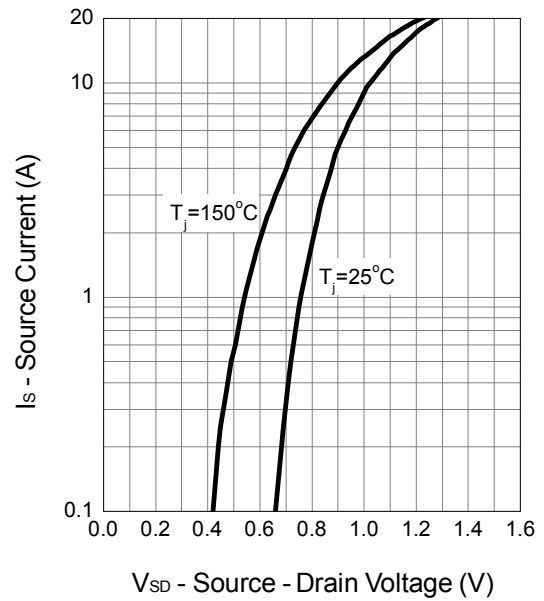


Typical Characteristics

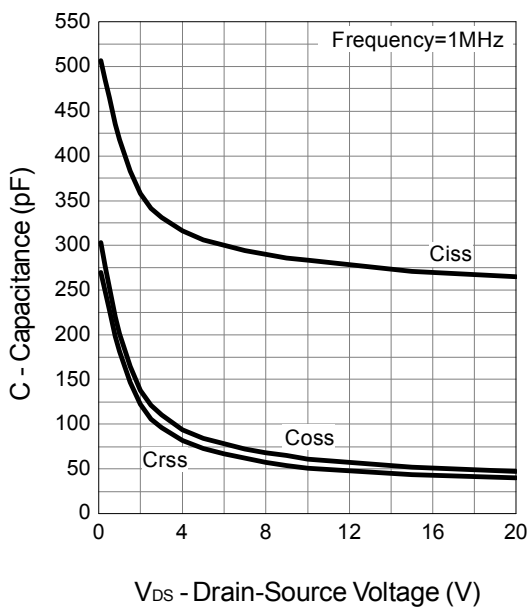
Drain-Source On Resistance



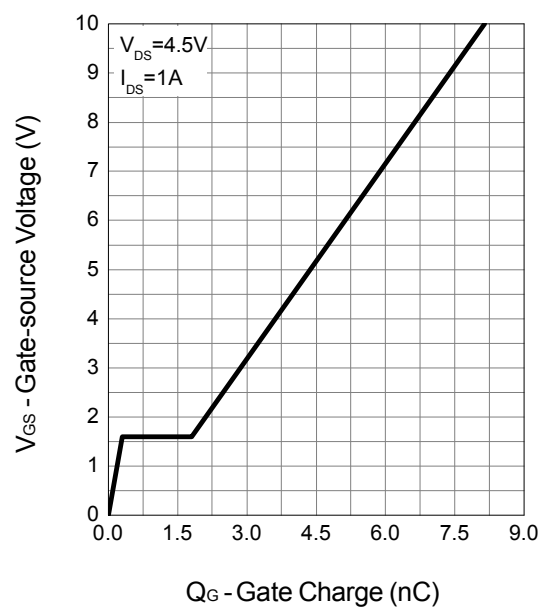
Source-Drain Diode Forward



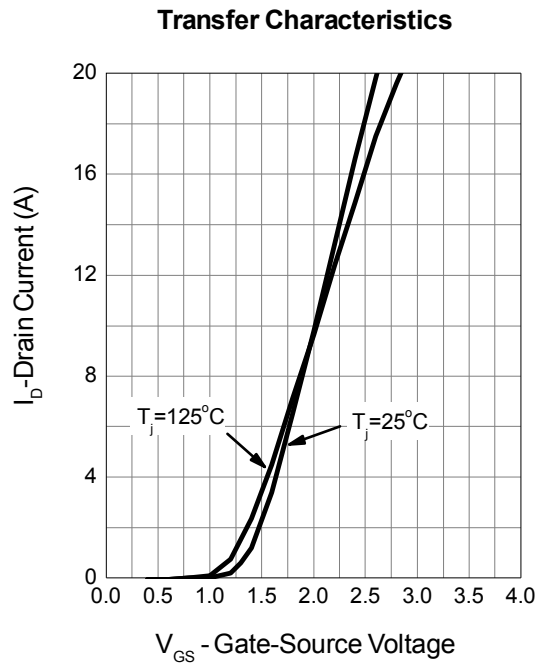
Capacitance



Gate Charge



Typical Characteristics





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